



## 15N70-MT

Preliminary

Power MOSFET

### 15A, 700V N-CHANNEL POWER MOSFET

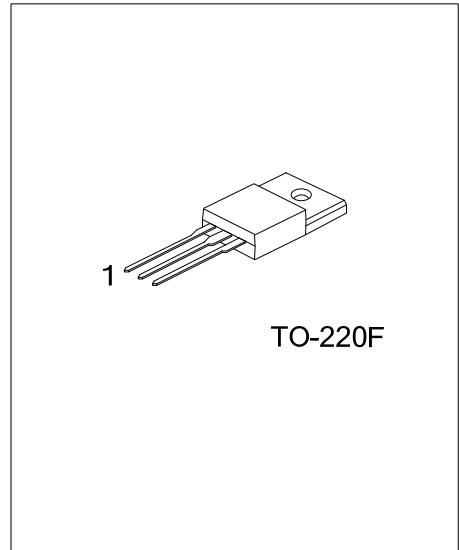
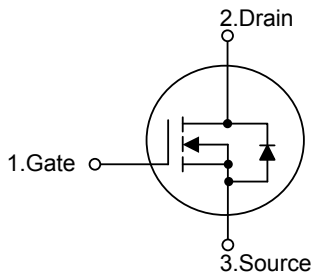
#### DESCRIPTION

The **UTC 15N70-MT** is a high voltage and high current power MOSFET, designed to have better characteristics, such as fast switching time, low gate charge, low on-state resistance and a high rugged avalanche characteristics. This power MOSFET is usually used at high speed switching applications in power supplies, PWM motor controls, high efficient DC to DC converters and bridge circuits.

#### FEATURES

- \*  $R_{DS(ON)} < 0.7 \Omega @ V_{GS} = 10V, I_D = 7.5A$
- \* Fast switching
- \* Improved dv/dt capability

#### SYMBOL



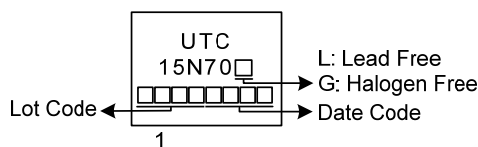
#### ORDERING INFORMATION

Ordering Number		Package	Pin Assignment			Packing
Lead Free	Halogen Free		1	2	3	
15N70L-TF3-T	15N70G-TF3-T	TO-220F	G	D	S	Tube

Note: Pin Assignment: G: Gate D: Drain S: Source

	<p>(1) T: Tube</p> <p>(2) TF3: TO-220F</p> <p>(3) G: Halogen Free and Lead Free, L: Lead Free</p>
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#### MARKING



■ ABSOLUTE MAXIMUM RATINGS ( $T_C = 25^\circ\text{C}$ , unless otherwise specified)

PARAMETER		SYMBOL	RATINGS	UNIT
Drain-Source Voltage		$V_{DSS}$	700	V
Gate-Source Voltage		$V_{GSS}$	$\pm 30$	V
Drain Current	Continuous	$I_D$	15	A
	Pulsed (Note 2)	$I_{DM}$	30	A
Avalanche Energy	Single Pulsed (Note 3)	$E_{AS}$	209	mJ
Peak Diode Recovery dv/dt (Note 4)		dv/dt	2.25	V/ns
Power Dissipation		$P_D$	39	W
Junction Temperature		$T_J$	+150	$^\circ\text{C}$
Storage Temperature		$T_{STG}$	-55 ~ +150	$^\circ\text{C}$

Notes: 1. Absolute maximum ratings are those values beyond which the device could be permanently damaged.

Absolute maximum ratings are stress ratings only and functional device operation is not implied.

2. Repetitive Rating: Pulse width limited by maximum junction temperature.
3.  $L = 10\text{mH}$ ,  $I_{AS} = 6.46\text{A}$ ,  $V_{DD} = 50\text{V}$ ,  $R_G = 25\ \Omega$  Starting  $T_J = 25^\circ\text{C}$
4.  $I_{SD} \leq 15\text{A}$ ,  $di/dt \leq 100\text{A}/\mu\text{s}$ ,  $V_{DD} \leq BV_{DSS}$ , Starting  $T_J = 25^\circ\text{C}$

■ THERMAL DATA

PARAMETER	SYMBOL	RATING	UNIT
Junction to Ambient	$\theta_{JA}$	62.5	$^\circ\text{C}/\text{W}$
Junction to Case	$\theta_{JC}$	3.2	$^\circ\text{C}/\text{W}$

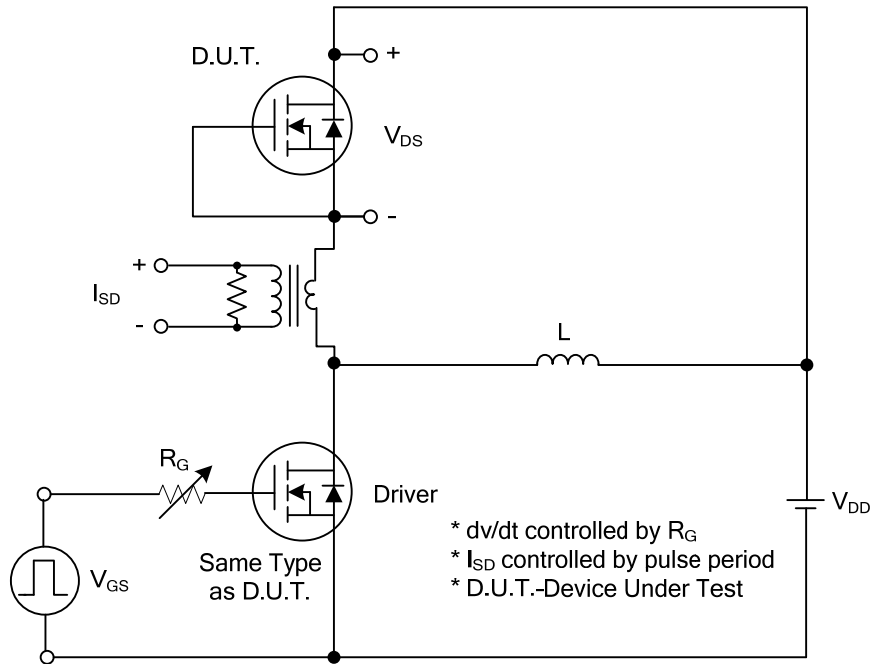
■ ELECTRICAL CHARACTERISTICS ( $T_J = 25^\circ\text{C}$ , unless otherwise specified)

PARAMETER	SYMBOL	TEST CONDITIONS	MIN	TYP	MAX	UNIT
<b>OFF CHARACTERISTICS</b>						
Drain-Source Breakdown Voltage	$BV_{DSS}$	$V_{GS}=0\text{V}$ , $I_D=250\mu\text{A}$	700			V
Drain-Source Leakage Current	$I_{DSS}$	$V_{DS}=700\text{V}$ , $V_{GS}=0\text{V}$			10	$\mu\text{A}$
Gate-Source Leakage Current	Forward	$I_{GSS}$			100	nA
	Reverse				-100	nA
<b>ON CHARACTERISTICS</b>						
Gate Threshold Voltage	$V_{GS(TH)}$	$V_{DS}=V_{GS}$ , $I_D=250\mu\text{A}$	2.0		4.0	V
Static Drain-Source On-State Resistance	$R_{DS(ON)}$	$V_{GS}=10\text{V}$ , $I_D=7.5\text{A}$			0.7	$\Omega$
<b>DYNAMIC CHARACTERISTICS</b>						
Input Capacitance	$C_{ISS}$	$V_{GS}=0\text{V}$ , $V_{DS}=25\text{V}$ , $f=1.0\text{MHz}$		2280		pF
Output Capacitance	$C_{OSS}$			200		pF
Reverse Transfer Capacitance	$C_{RSS}$			12		pF
<b>SWITCHING CHARACTERISTICS</b>						
Total Gate Charge (Note 1)	$Q_G$	$V_{DS}=100\text{V}$ , $V_{GS}=10\text{V}$ , $I_D=15\text{A}$ $I_G=1\text{mA}$ (Note 1, 2)		47		nC
Gate-Drain Charge	$Q_{GD}$			13		nC
Gate-Source Charge	$Q_{GS}$			13		nC
<b>SWITCHING CHARACTERISTICS</b>						
Turn-on Delay Time (Note 1)	$t_{D(ON)}$	$V_{DS}=100\text{V}$ , $V_{GS}=10\text{V}$ , $I_D=15\text{A}$ , $R_G=25\ \Omega$ (Note 1, 2)		30		ns
Rise Time	$t_R$			24		ns
Turn-off Delay Time	$t_{D(OFF)}$			160		ns
Fall-Time	$t_F$			47		ns
<b>SOURCE- DRAIN DIODE RATINGS AND CHARACTERISTICS</b>						
Maximum Body-Diode Continuous Current	$I_S$				15	A
Maximum Body-Diode Pulsed Current	$I_{SM}$				30	A
Drain-Source Diode Forward Voltage (Note 1)	$V_{SD}$	$V_{GS}=0\text{V}$ , $I_S=15\text{A}$			1.4	V
Reverse Recovery Time (Note 1)	$t_{rr}$	$V_{GS}=0\text{V}$ , $I_S=15\text{A}$		456		ns
Reverse Recovery Charge	$Q_{rr}$	$di/dt=100\text{A}/\mu\text{s}$ (Note1)		7.3		$\mu\text{C}$

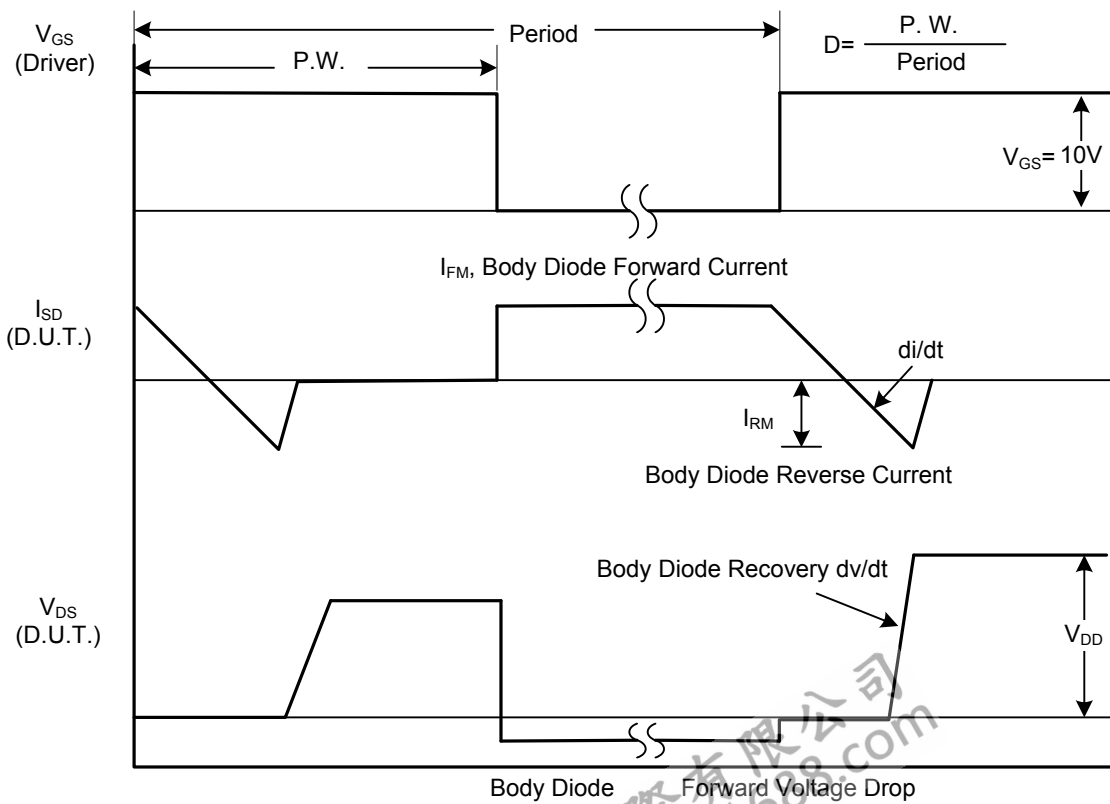
Notes: 1. Pulse Test : Pulse width  $\leq 300\mu\text{s}$ , Duty cycle  $\leq 2\%$ .

2. Essentially independent of operating temperature.

■ TEST CIRCUITS AND WAVEFORMS

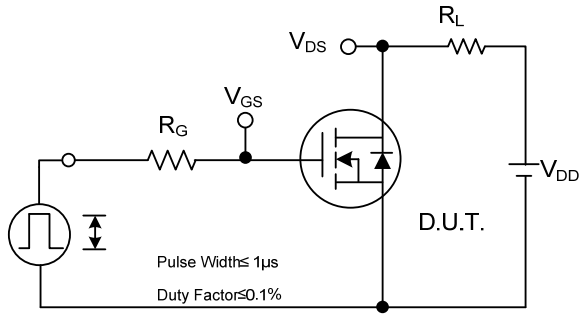


Peak Diode Recovery  $dv/dt$  Test Circuit

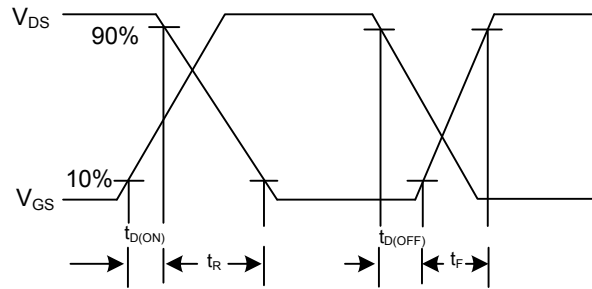


Peak Diode Recovery  $dv/dt$  Waveforms

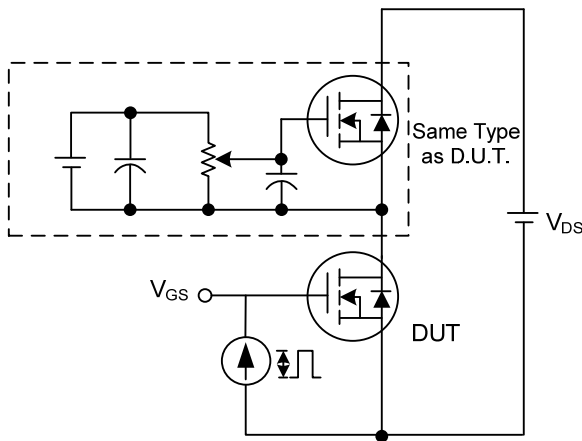
TEST CIRCUITS AND WAVEFORMS



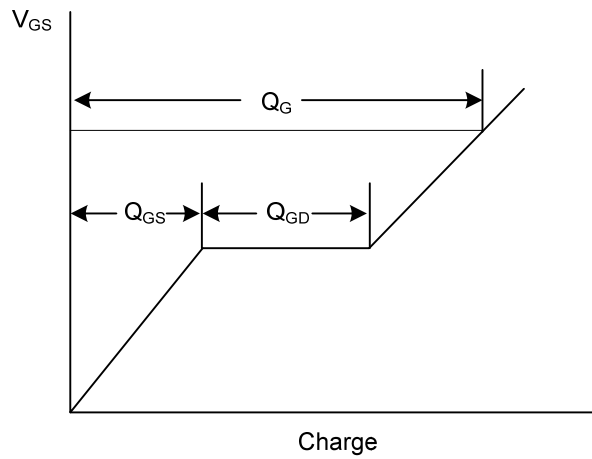
Switching Test Circuit



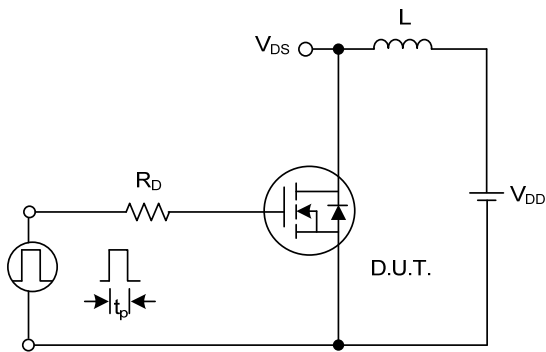
Switching Waveforms



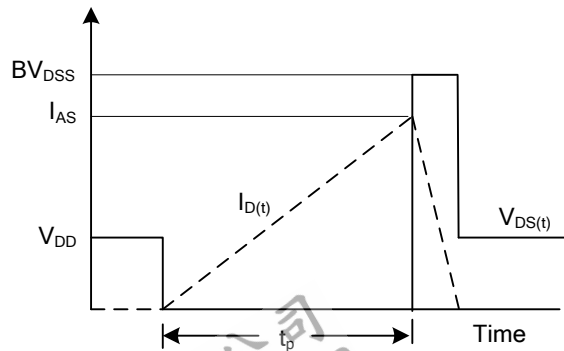
Gate Charge Test Circuit



Gate Charge Waveform



Unclamped Inductive Switching Test Circuit



Unclamped Inductive Switching Waveforms

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